

# IMiD 2023

The 23rd International Meeting on Information Display  
August 22-25, 2023 / BEXCO, BUSAN, KOREA

|                          |  |
|--------------------------|--|
| <b>Session Title:</b>    | 17. Oxide TFT III  |
| <b>Session Date:</b>     | August 24 (Thu.), 2023   |
| <b>Session Time:</b>     | 09:00-10:20  |
| <b>Session Room:</b>     | Room A (211~213)   |
| <b>Session Chair(s):</b> | Prof. Hyunseong Kum (Yonsei Univ., Korea)<br>Dr. Jae Hoon Jung (APS Research, Korea) |

[A17-1] [Invited] 09:00-09:25

Field-Effect Emission or Field-Effect Detection Enabled by Oxide Transistor Hybrid Integration

Chuan Liu (Sun Yat-sen Univ., China)

[A17-2] 09:25-09:40

Vertical Oxide Channel Thin-Film Transistors for High Density OLED Pixel Array

Jong-Heon Yang, Yong-Hae Kim, Jae-Eun Pi, Hee-Ok Kim, Chan-mo Kang, Hyunsu Cho, Kang Me Lee, Jaehyun Moon, Seung-Youl Kang (ETRI, Korea), Nak-Jin Seong, Young Ha Kwon, Kyu-Jeong Choi (NCD Co., Ltd., Korea), and Chi-Sun Hwang (ETRI, Korea)

[A17-3] 09:40-09:55

Performance Analysis of Indium-Tin-Zinc-Oxide-Based 2T0C DRAM with Low Leakage Current for Improved Retention Time

Seong Ui An, Yo Seop Chi, Taewon Jin (Hanyang Univ., Korea), Dae-Hwan Ahn, Jae-hoon Han (KIST, Korea), and Younghyun Kim (Hanyang Univ., Korea)

[A17-4] [Invited] 09:55-10:20

High-Mobility Thin-Film Transistors with Polycrystalline  $\text{In}_2\text{O}_3:\text{H}$  Channel Deposited by Pulsed Laser Deposition under High-Base Pressure

Yusaku Magari and Hiromichi Ohta (Hokkaido Univ., Japan)